

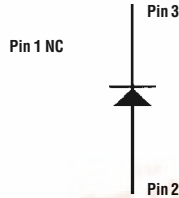


Data Sheet

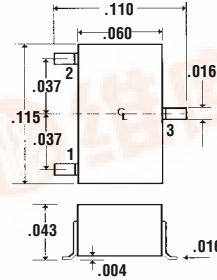
200 mW EPITAXIAL PLANAR DIODES

FMBBAS16

Description



Mechanical Dimensions



Features

- PLANAR PROCESS
- 200 mW POWER DISSIPATION

- INDUSTRY STANDARD SOT-23 PACKAGE
- MEETS UL SPECIFICATION 94V-0

Electrical Characteristics @ 25°C.	FMBBAS16	Units
Maximum Ratings	FMBBAS16	
Peak Reverse Voltage... V_{RM}	85	Volts
RMS Reverse Voltage... $V_{R(rms)}$	75	Volts
Average Forward Rectified Current... I_O	215	mAmps
Non-Repetitive Peak Forward Surge Current... I_{FSM}	4	Amps
Forward Voltage... V_F @ $I_F = 150$ mA	1.25	Volts
DC Reverse Current... I_R @ $V_R = 75$ V	5.0	μAmps
Power Dissipation... P_D	200	mW
Frequency...F	100	MHz
Typical Junction Capacitance... C_j	2.0	pF
Reverse Recovery Time... t_{RR}	4.0	nS
Operating Temperature Range... T_J	-25 to 85	°C
Storage Temperature Range... T_{STRG}	-65 to 150	°C

Device Under Test

